

Microscopy and Spectroscopy to Characterize Processed Materials

Alice Kunin

Assistant Professor

Department of Chemistry

Princeton University

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Which characterization technique is the right one for my material?

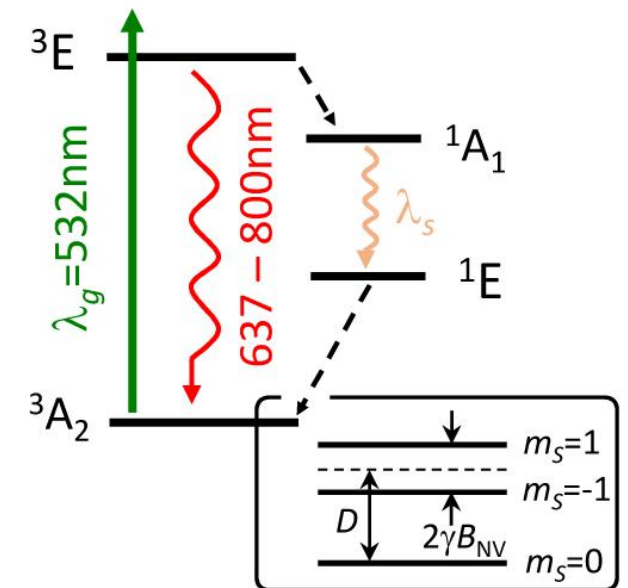
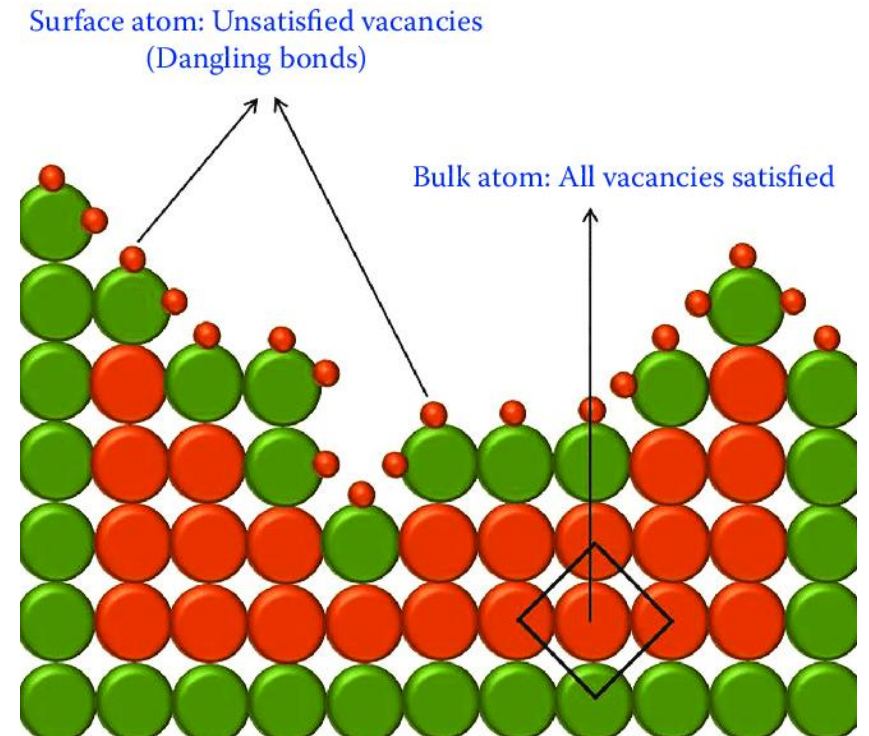
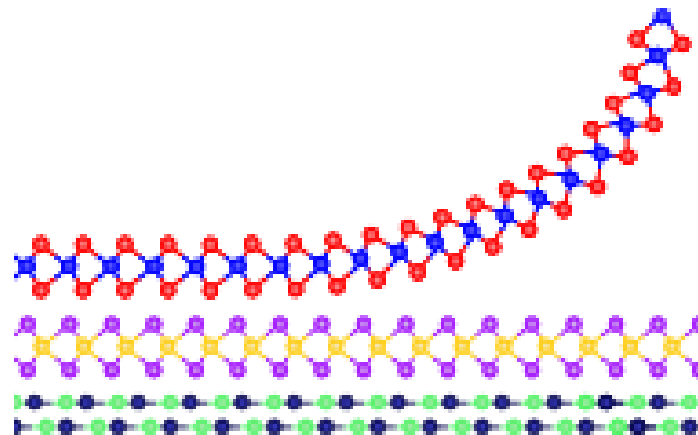
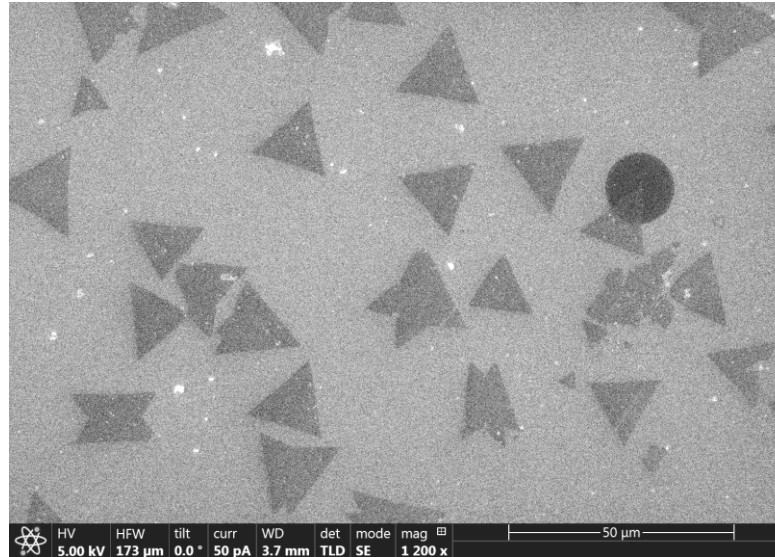
That depends a great deal on what it is you want to learn!

This lecture: a brief roadmap to this dense forest of materials science characterization techniques



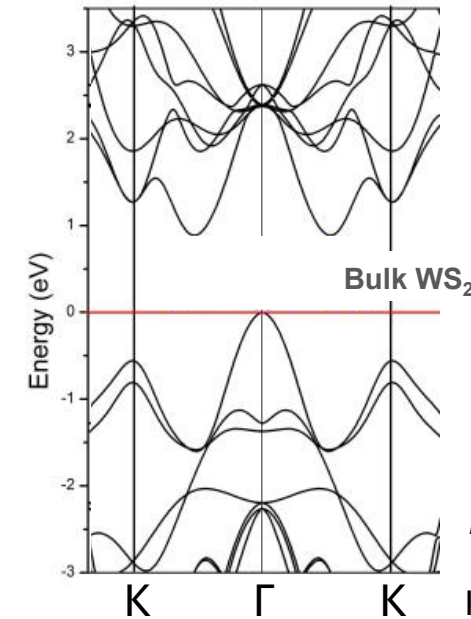
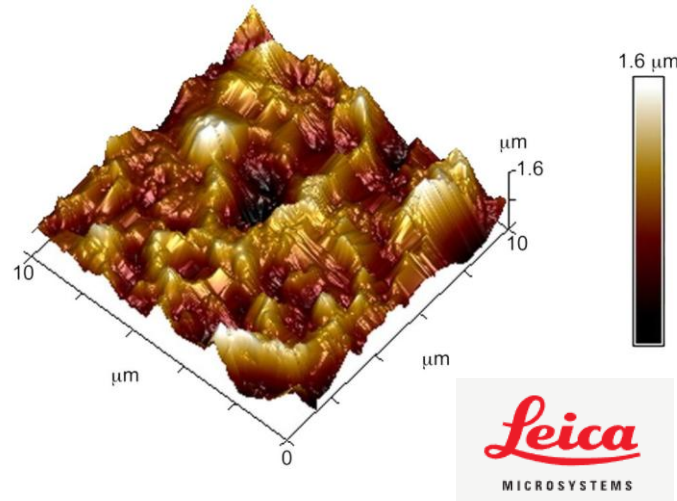
Practical considerations

- Size
- Thickness (/thinness, substrate)
- Surface vs. bulk
- Resolution (spatial, energy, etc...)



Philosophical considerations

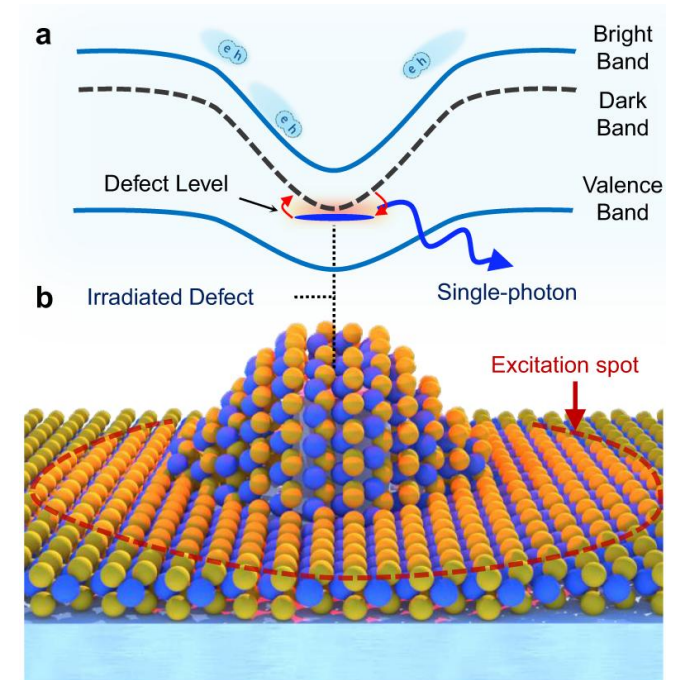
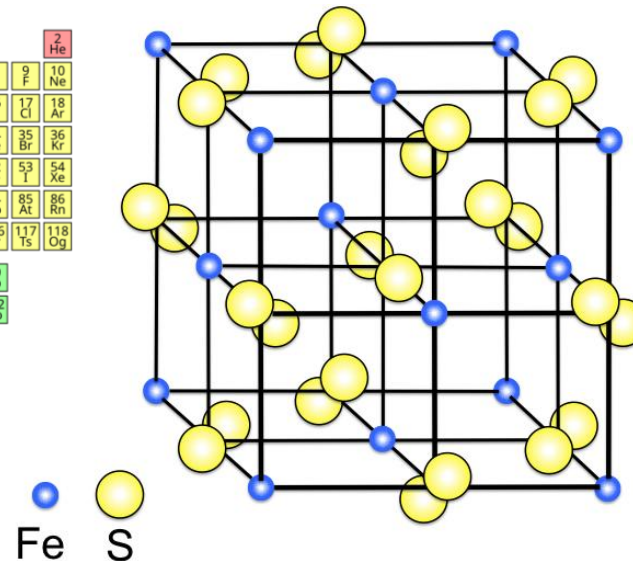
- Morphology
- Composition
- Lattice structure
- Electronic structure
- Dynamics, light-matter interactions



H. Terrones et al. *Sci Rep.* **3**, 1549 (2013)

K. Parto et al. *Nat. Commun.* **12**, 2, 3585 (2021)

A standard periodic table of elements, color-coded by groups. The elements are arranged in rows and columns, with atomic numbers and chemical symbols.



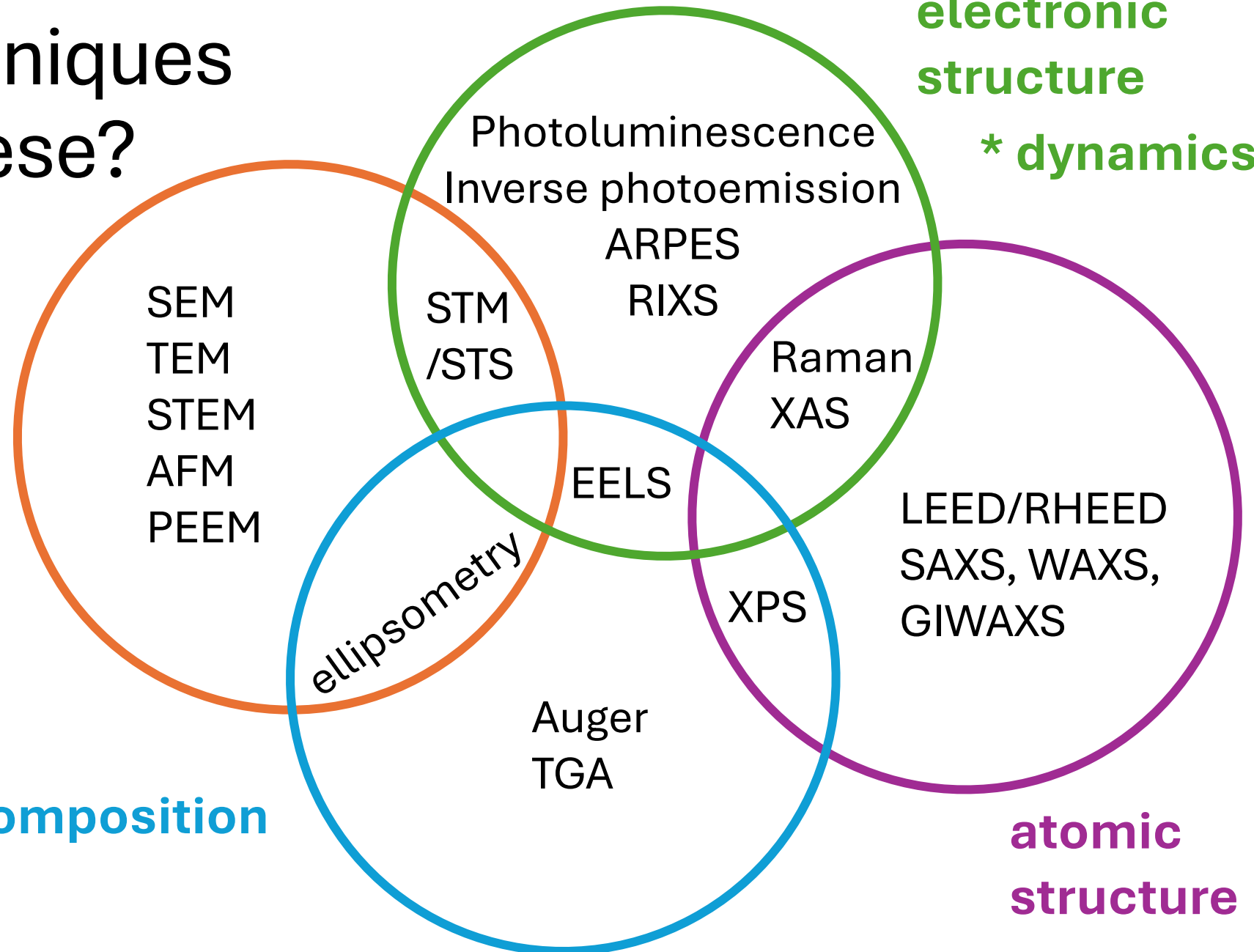
Which techniques address these?

morphology

composition

**electronic
structure**
*** dynamics**

**atomic
structure**



Not exhaustive!

Techniques by type of probe

optical

Photoluminescence
Raman
XAS, NEXAFS
Ellipsometry
Reflectivity

photoelectric

XPS/UPS
ARPES
PEEM

scanning probe

STM
AFM
SNOM
Tip-enhanced Raman

time-resolved

PL, Raman
XAS
XPS, ARPES
PEEM
STM, SNOM
RIXS

...

electron

LEED/RHEED
Auger
EELS
Inverse photoemission
(S)(T)EM

scattering

SAXS, WAXS, GIWAXS
RIXS
Neutron

thermal

DSC
TGA
TPD

Not exhaustive!



Microscopy

Magnify and resolve small features

optical

electron

scanning probe



spatial resolving power

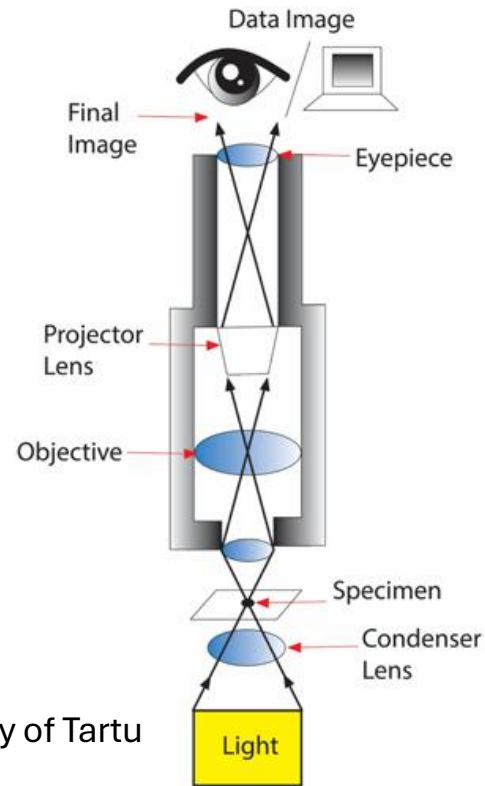


relative ease of use, speed of measurement

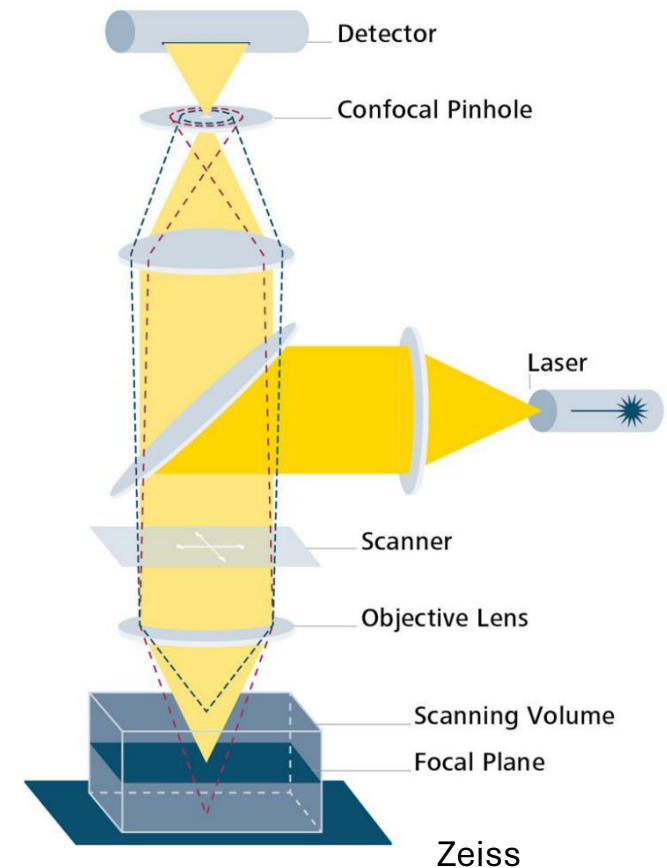
Optical microscopy



University of Tartu



- Resolution down to ~ 200 nm if perfect
- Consider: if your sample is very thin, it may have very poor optical contrast!

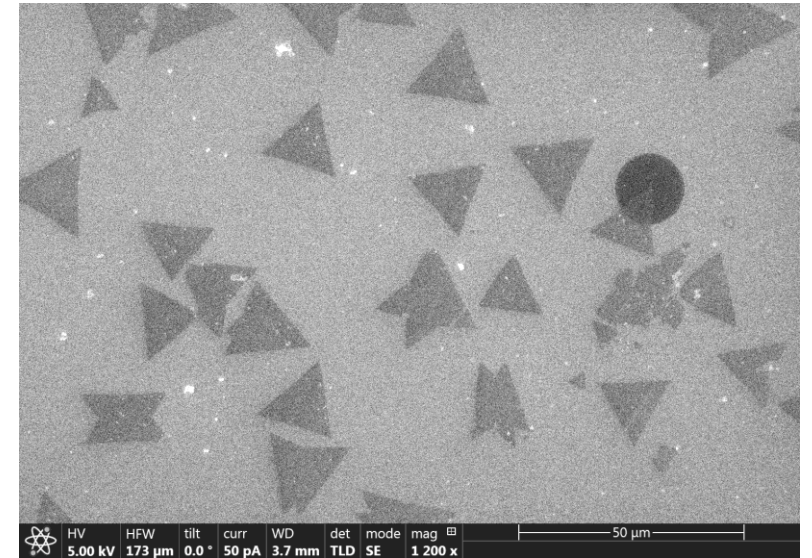


Zeiss

- Can be easily coupled with lasers to combine microscopy with laser spectroscopic approaches

Electron Microscopy

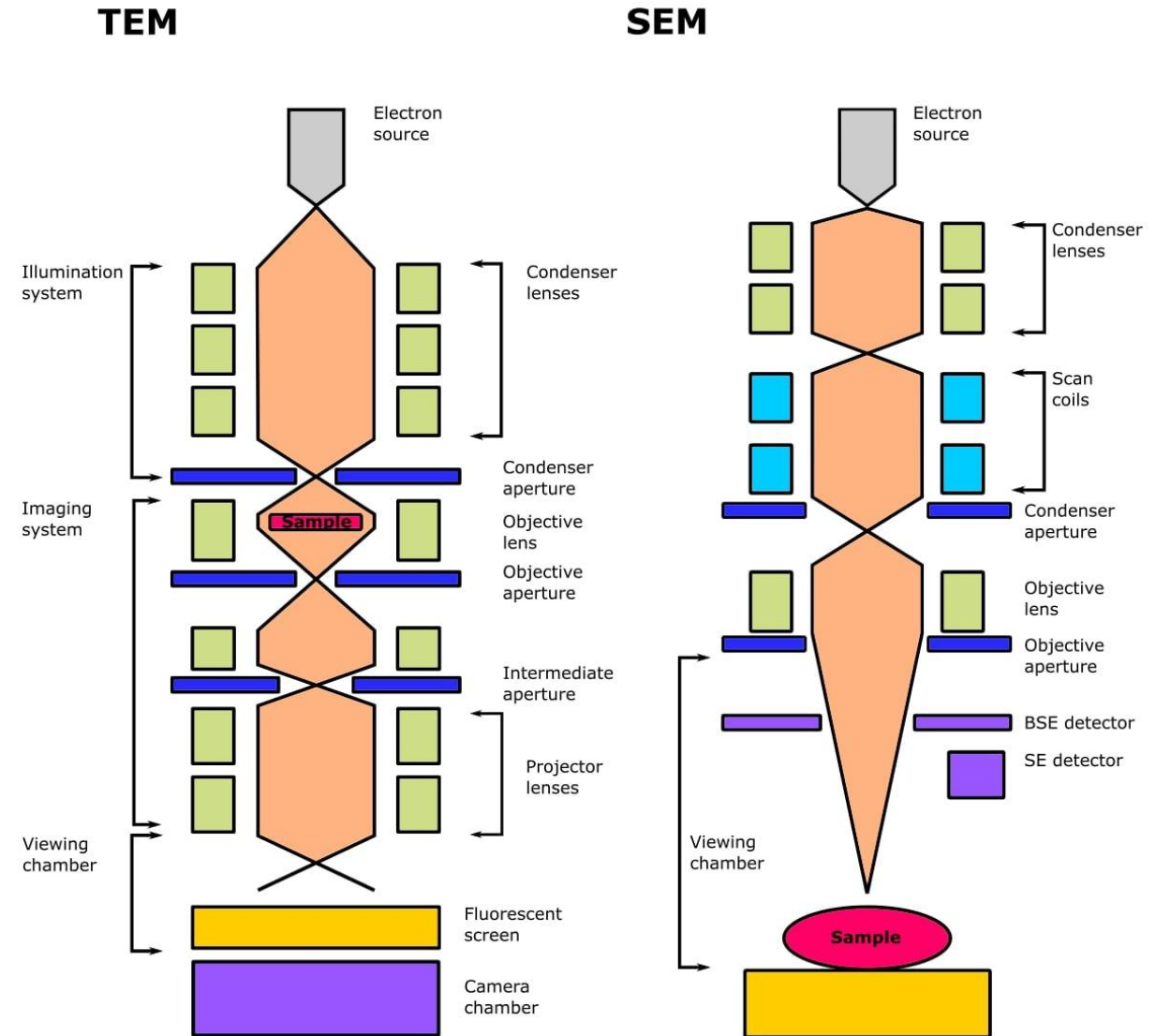
- Use a beam of electrons to illuminate a sample, a series of electro-optic lenses to focus and control the beam
- Resolution typically few to 10s of nm depending on system
- Vacuum techniques, samples should be reasonably conductive (or sputter coated)
- Consider checking out <https://myscope.training/> to practice aligning imaging columns



Monolayer WS₂ grown flakes in SEM

Electron Microscopy

- Transmission vs. scanning
- TEM: electrons transmit and are imaged to a camera, where contrast is governed by electrons scattered/absorbed by the sample
- SEM: detect secondary and backscattered electrons from the sample surface
- TEM can offer higher resolution, but samples must be thin and prepared on special grids (tricky)
- STEM variation combines both – same sample requirements as TEM, but can achieve higher resolution



Scanning Probe Microscopy

A very diverse family of techniques typically capable of achieving sub-nm resolution of features on the surface of materials

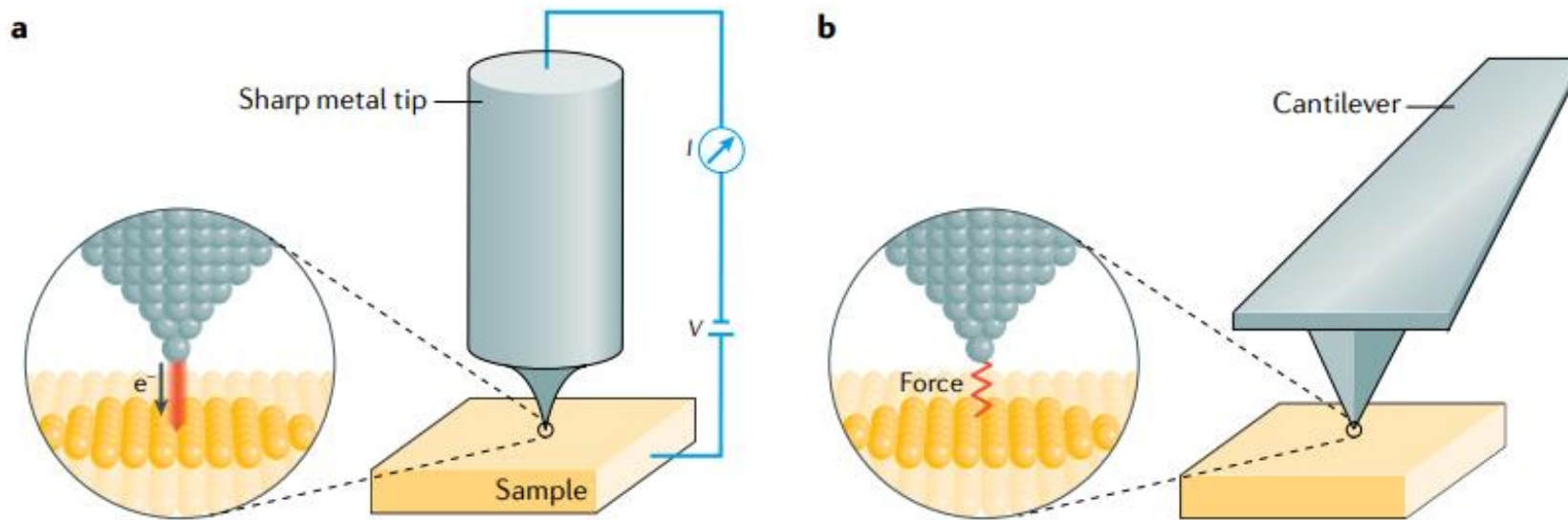
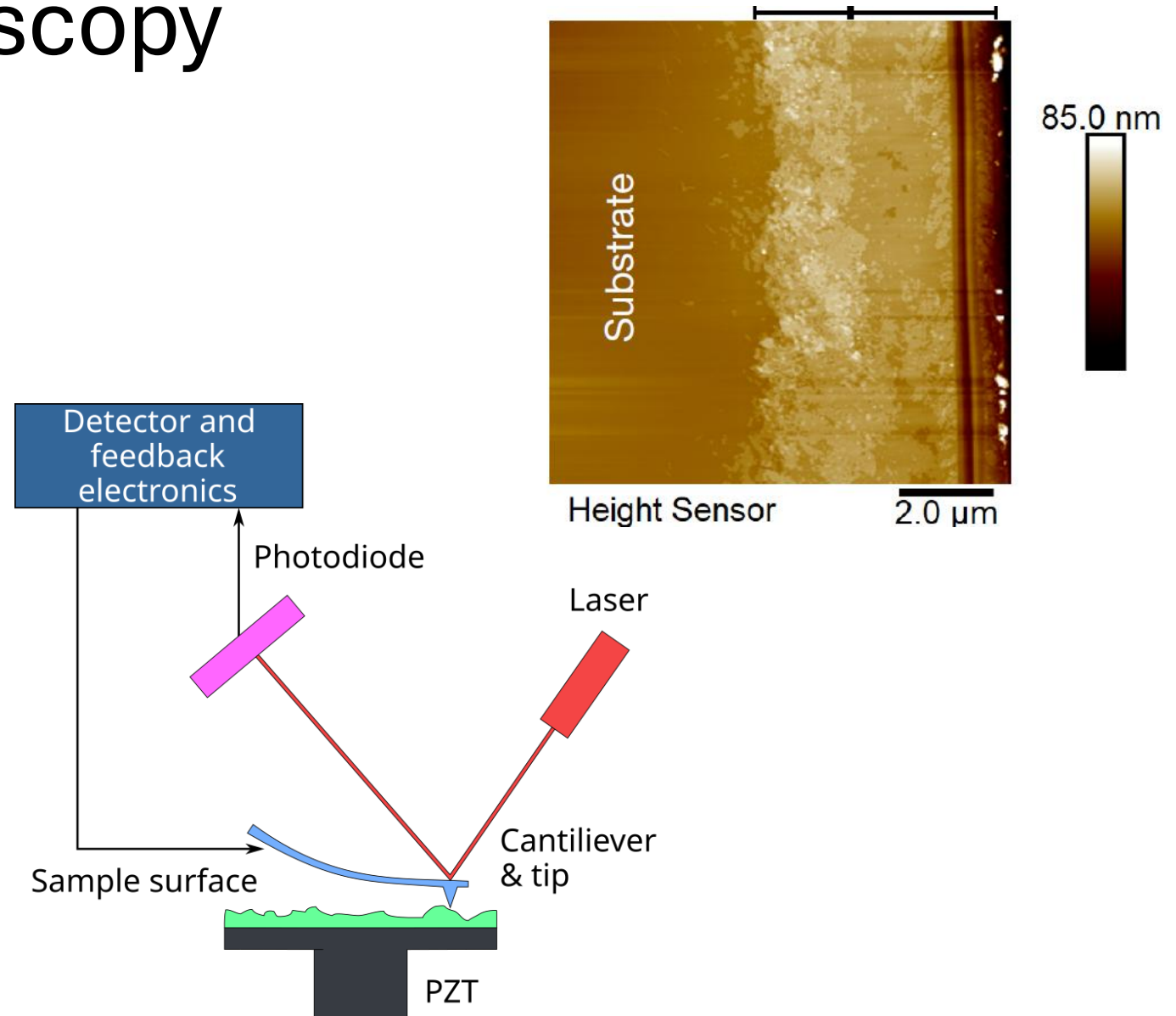


Fig. 1 | **Basic set-up for scanning probe microscopy.** Scanning tunnelling microscopy (STM) and atomic force microscopy (AFM) both use a tip to scan the sample. Both techniques use different feedback signals to maintain constant tip-sample interaction, but their basic principle of operation and image acquisition mechanisms are similar. **a** | STM collects the tunnelling current between the tip apex and the sample when a bias voltage is applied. **b** | AFM detects local forces and corresponding mechanical parameters through a spring-like cantilever.

Atomic Force Microscopy

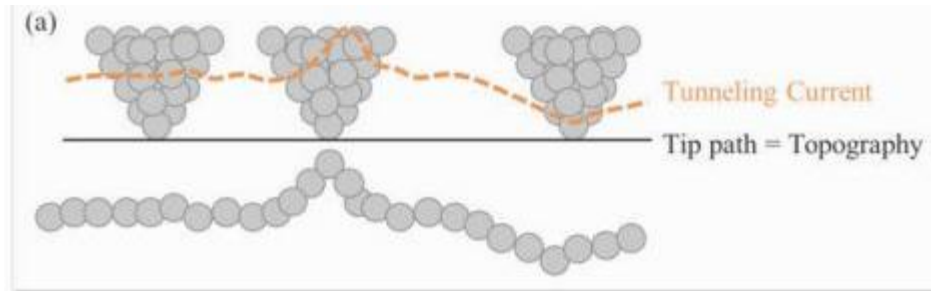
- In contact AFM, the tip directly contacts the surface, providing a highly sensitive probe of surface roughness (sub nm)
- Ambient technique suitable for a range of samples from conducting to insulating



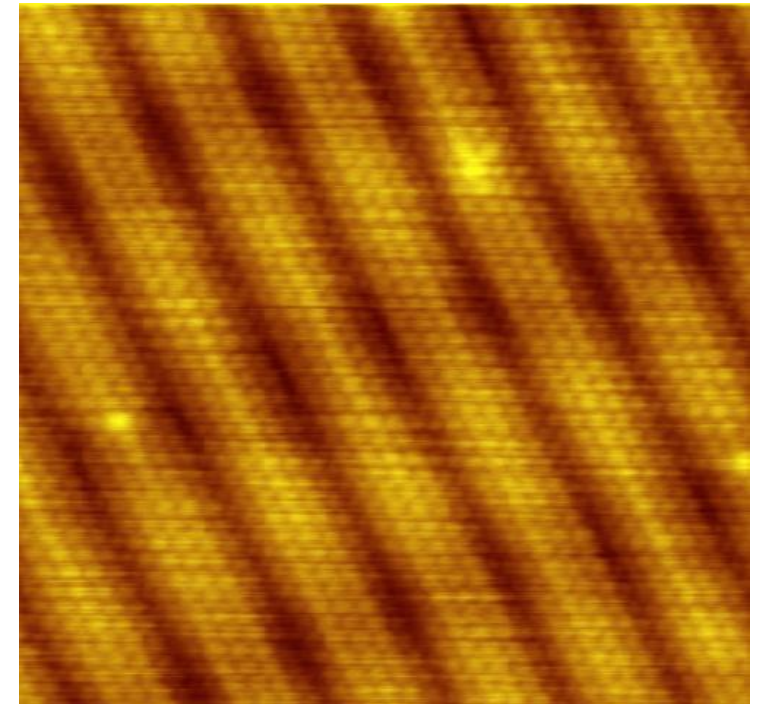
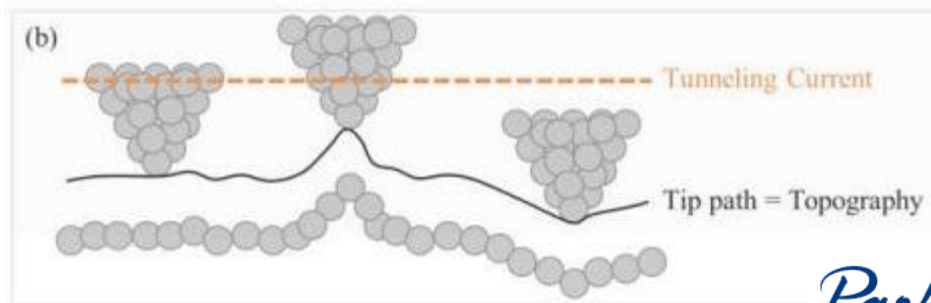
Scanning Tunneling Microscopy

- Most typically requires an ultrahigh vacuum environment and cryogenically cooled temperatures
- Strict: sample must have a clean surface and be conductive at these temperatures. Also, slow!

Constant height mode



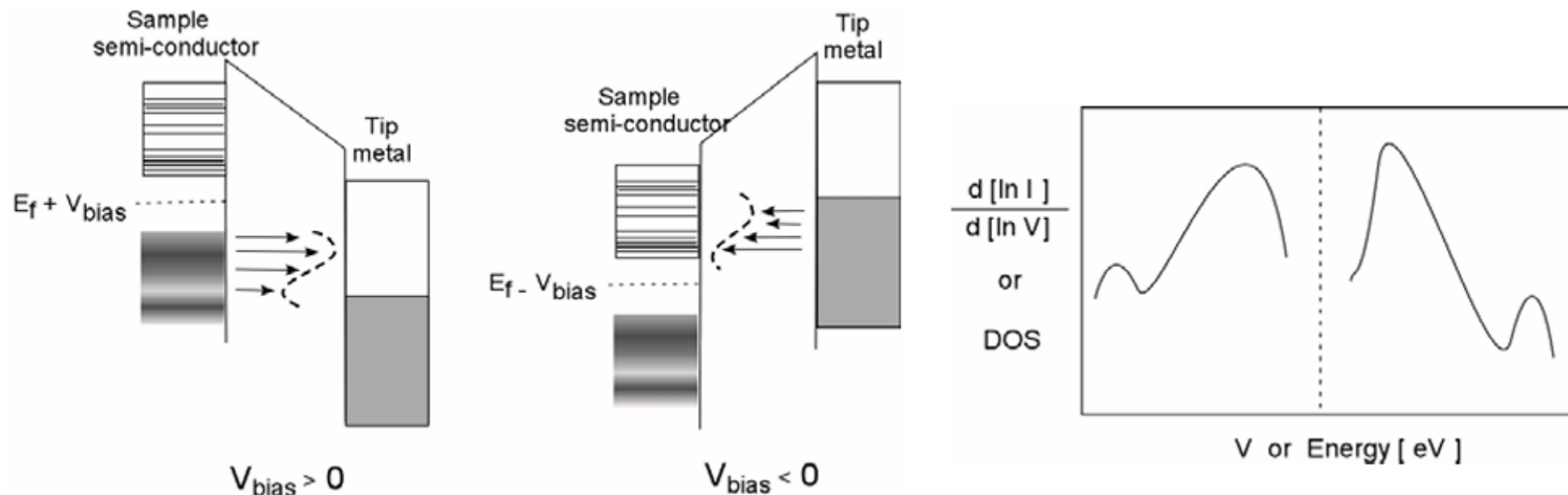
Constant current mode



Au (100) surface (Erwin Rossen)

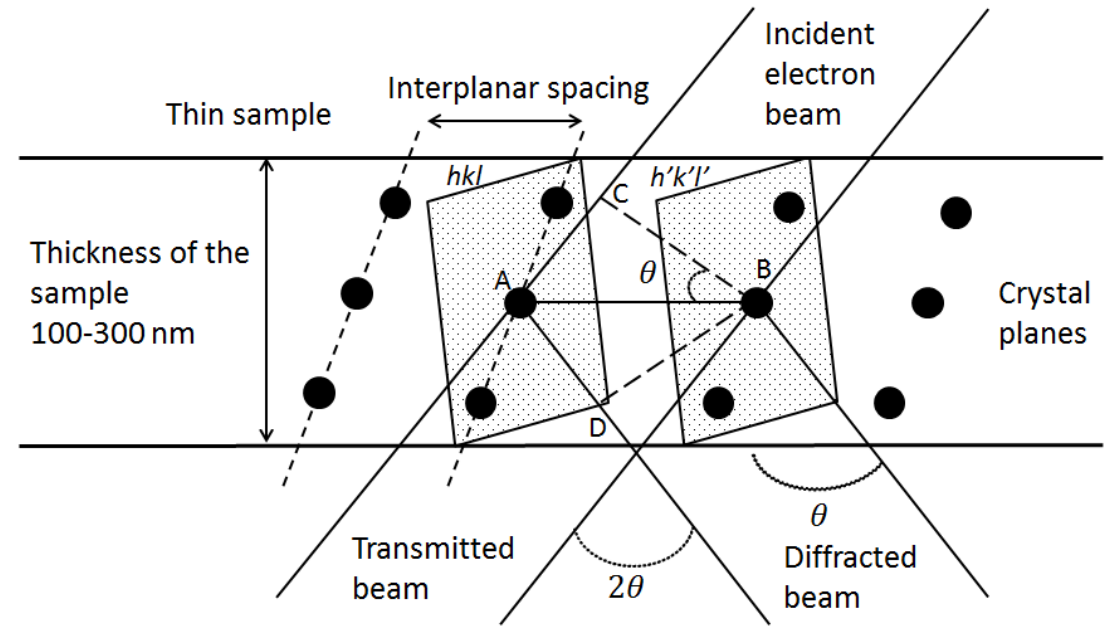
Scanning Tunneling Spectroscopy

- Bias voltage allows current flow between tip and sample without contact via quantum tunneling through the barrier
- To map the local density of states, fix the tip height and measure the change in electron tunneling current as a function of electron energy (tip bias)



Electron Diffraction

- Sensitive approach for measuring crystal lattice structure
- Ultrahigh vacuum technique
- Can be destructive to the sample
- There are also x-ray diffraction + scattering related variants (SAXS, WAXS, GIWAXS)



M. A. Asadabad and M. J. Eskandari. *Modern Electron Microscopy in Physical and Life Sciences*, 2016.

→ (should I use electrons or x-rays? If the sample is small or thin (2D), you must use electrons. If the sample is thicker/3D, go for x-rays)

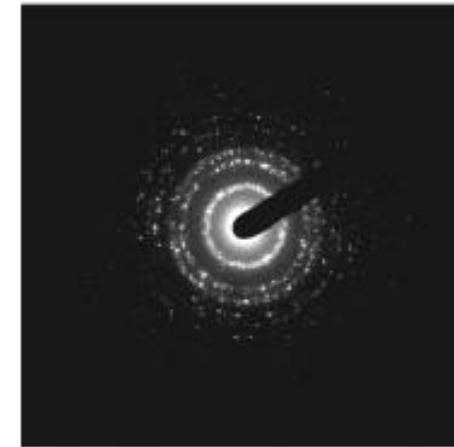
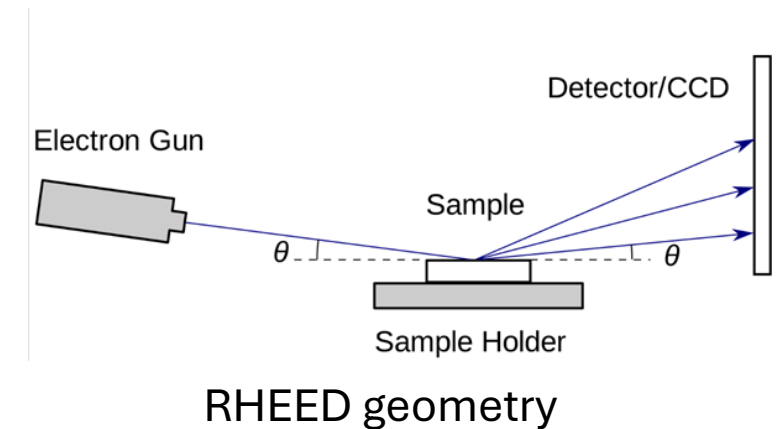
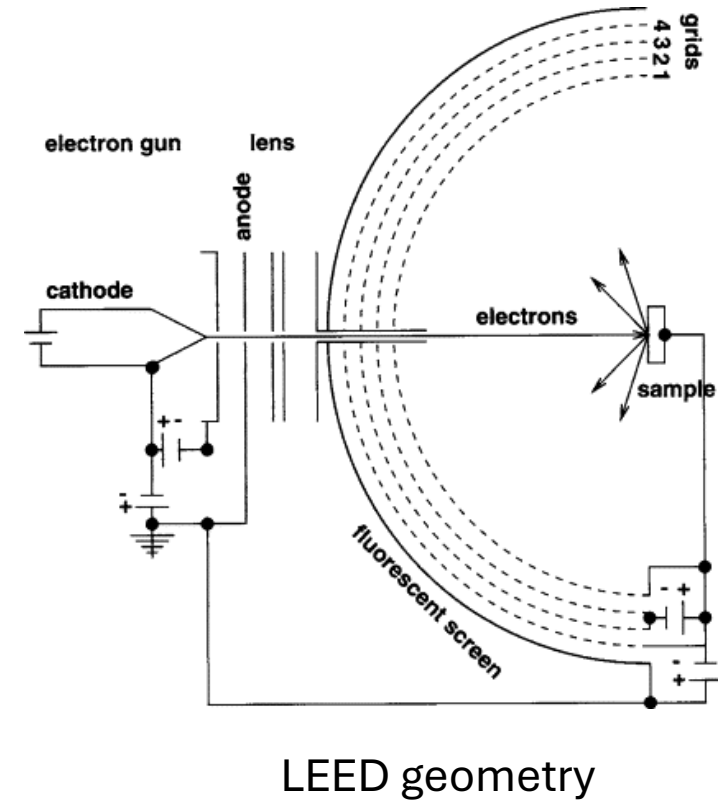


Fig. 4. Example of diffraction patterns: Crystalline Si (left), polycrystalline Si (centre), and quartz glass (right)

LEED, RHEED

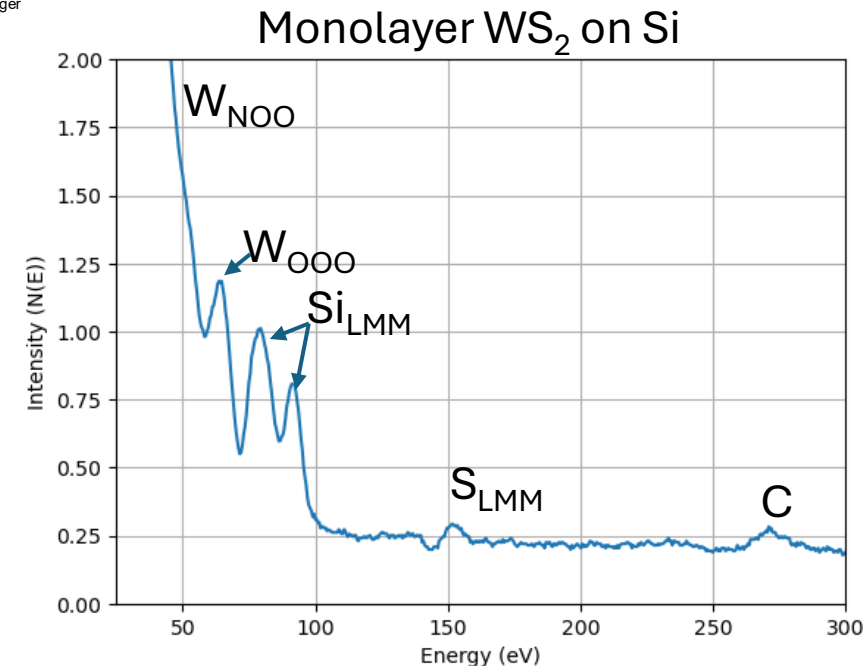
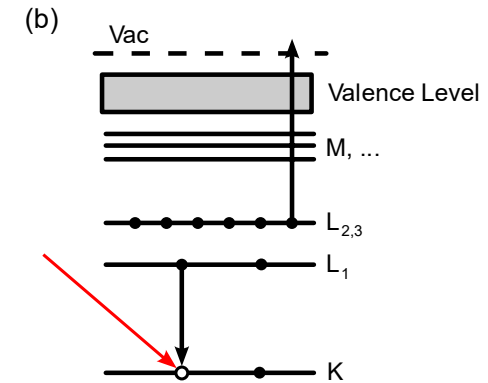
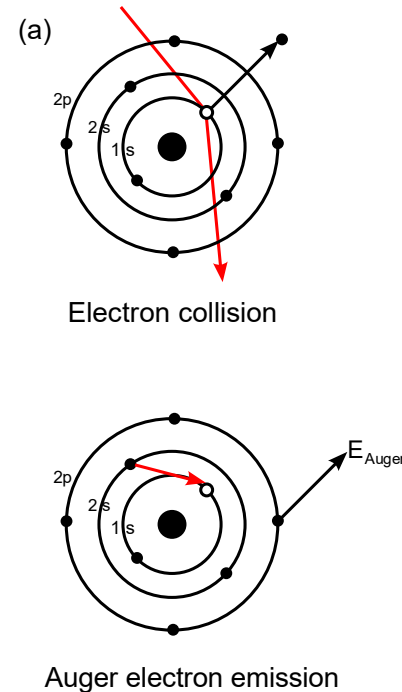
- LEED (Low-Energy Electron Diffraction) and RHEED (Reflection High-Energy Electron Diffraction) are both powerful tools for observing surface crystal, growth, and cleanliness
- The lower energy range of LEED ($\sim 10\text{-}200\text{ eV}$) compared to RHEED ($\sim \text{keV}$) makes it more surface sensitive (can identify surface reconstruction)
- The grazing reflection geometry of RHEED is more amenable for in situ measurements during growth or processing



Elemental Analysis with Electrons

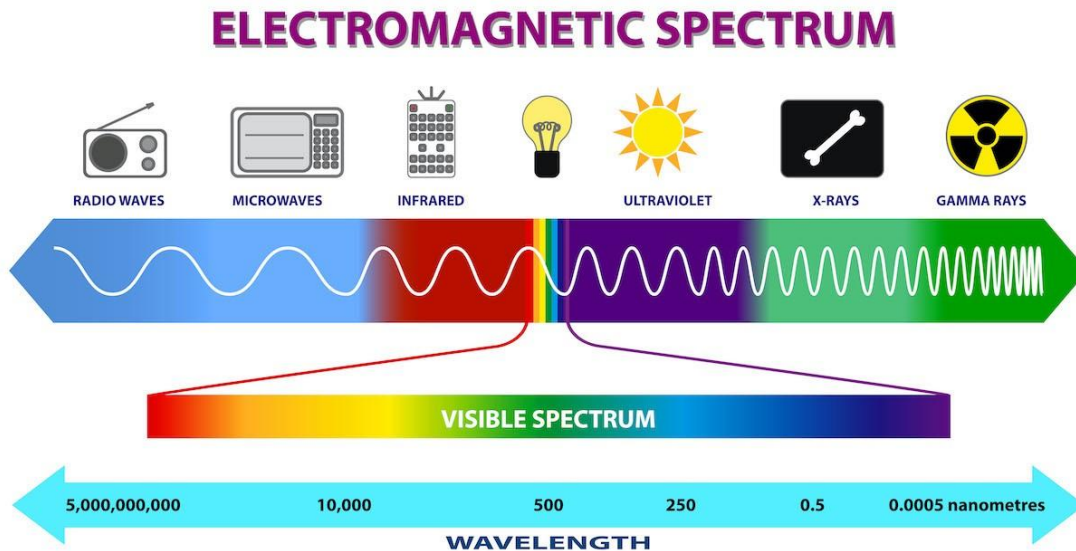
Auger electron spectroscopy

- Relaxation of outer shell electron to a core hole leads to emission of Auger electrons with characteristic energies
- Auger transitions are labeled according to the shells involved in the process
 - Process to the right would be labeled $KL_1L_{2,3}$
- Transition energies are element specific but subject to shifts based on chemical environment
- Surface-sensitive vacuum technique often coupled with LEED/RHEED instruments

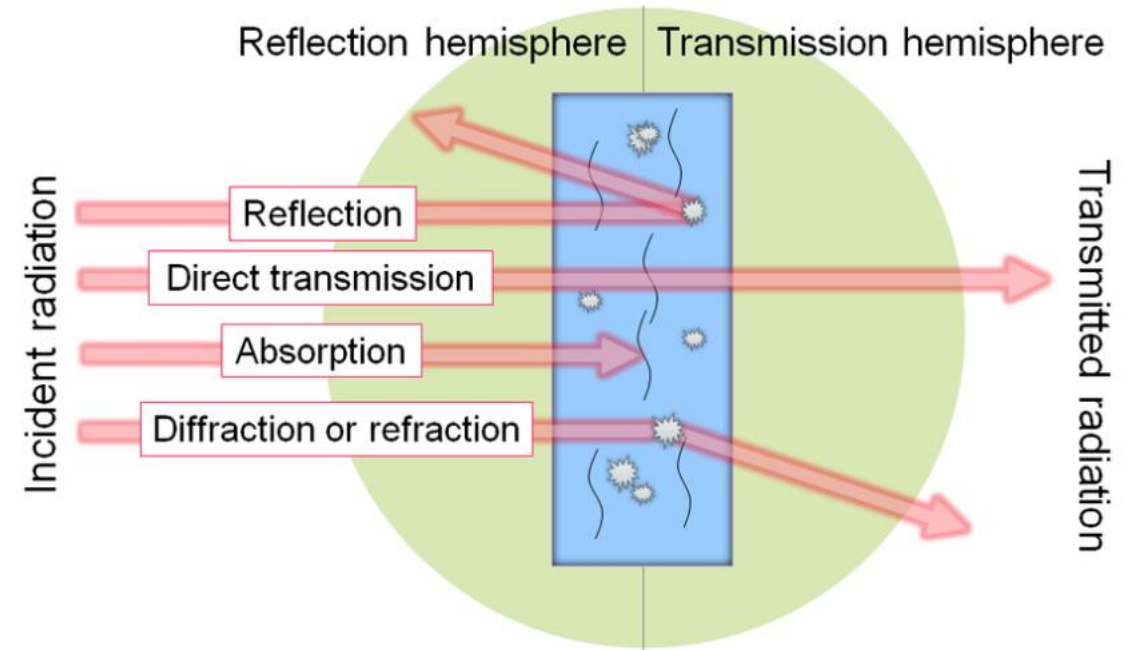


Spectroscopy

- Using electromagnetic radiation to probe the properties of matter (often electronic)
- Broadly categorized either by the range of the electromagnetic spectrum used, or by the type of interaction (absorption, fluorescence, Raman, etc.)



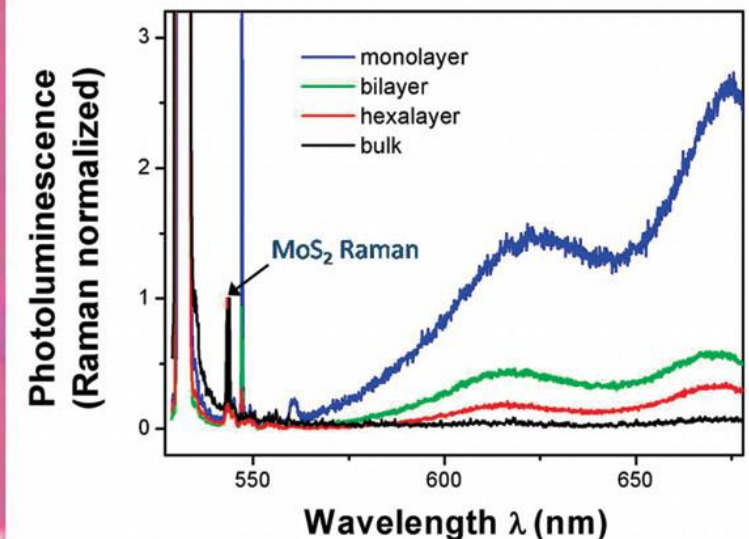
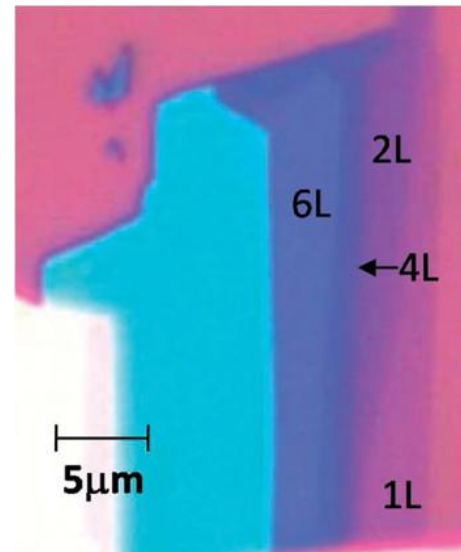
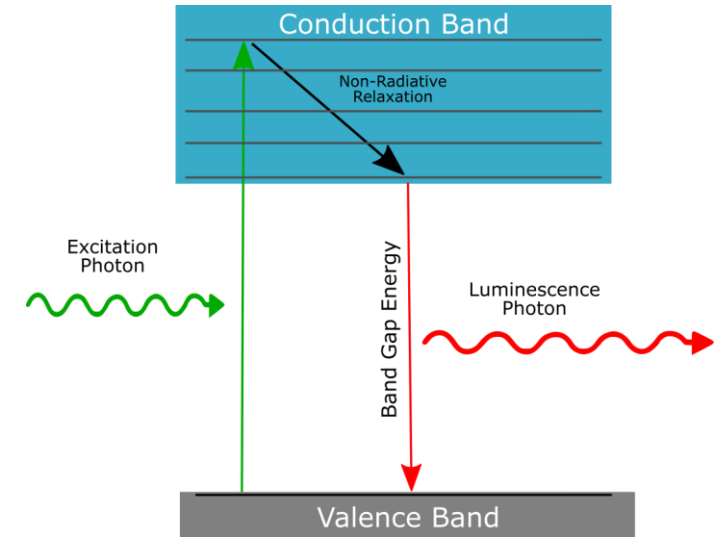
Getty



Kari Hyll

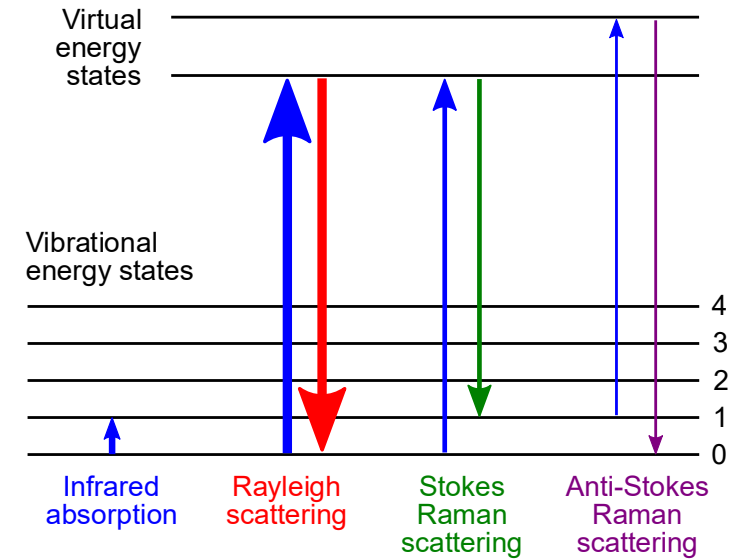
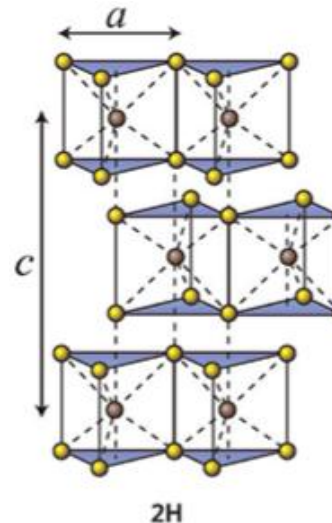
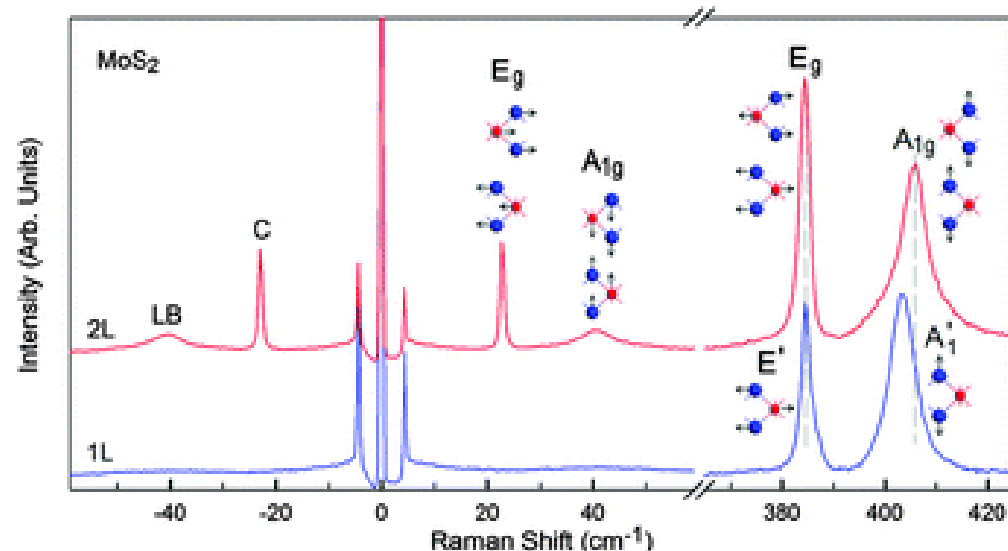
Optical Photoluminescence

- Used to probe optical band gaps and optical transition energies for semiconducting systems
- Easy to perform with visible lasers in commercial instruments, does not carry surface cleanliness requirements of other techniques
- Note that indirect band gap semiconductors may have weak signatures...
- Time-resolved photoluminescence is a popular variant in which the optical excitation is synchronized with photoluminescence recording



Raman Spectroscopy

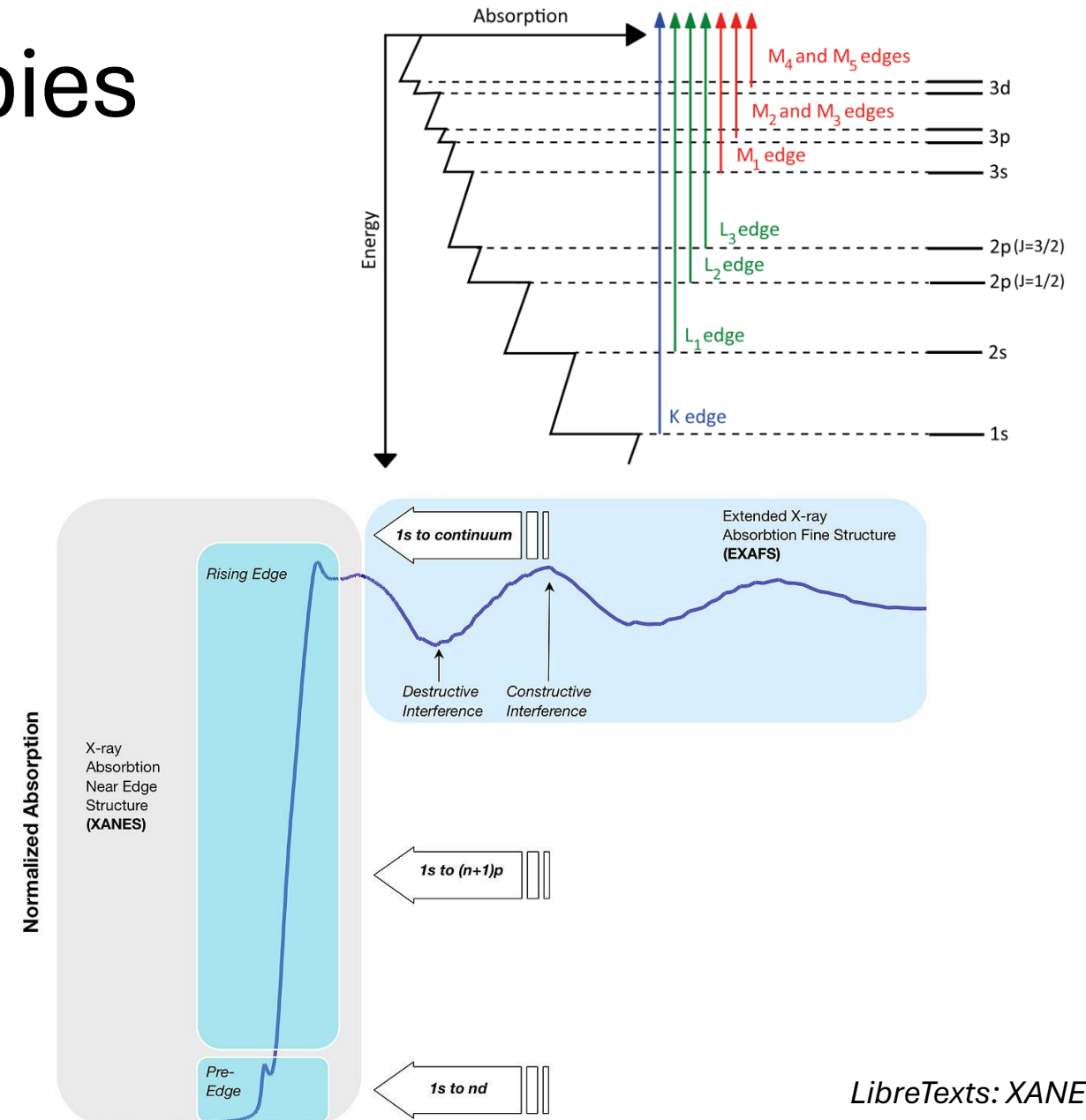
- Visible, IR, UV, or x-ray light can be used
- Inelastic scattering with material phonons: Raman scattering
- Sensitive to material vibrational modes
- Can be very useful for identifying number of layers in low-dimensional/thin materials



Wikipedia: Raman spectroscopy

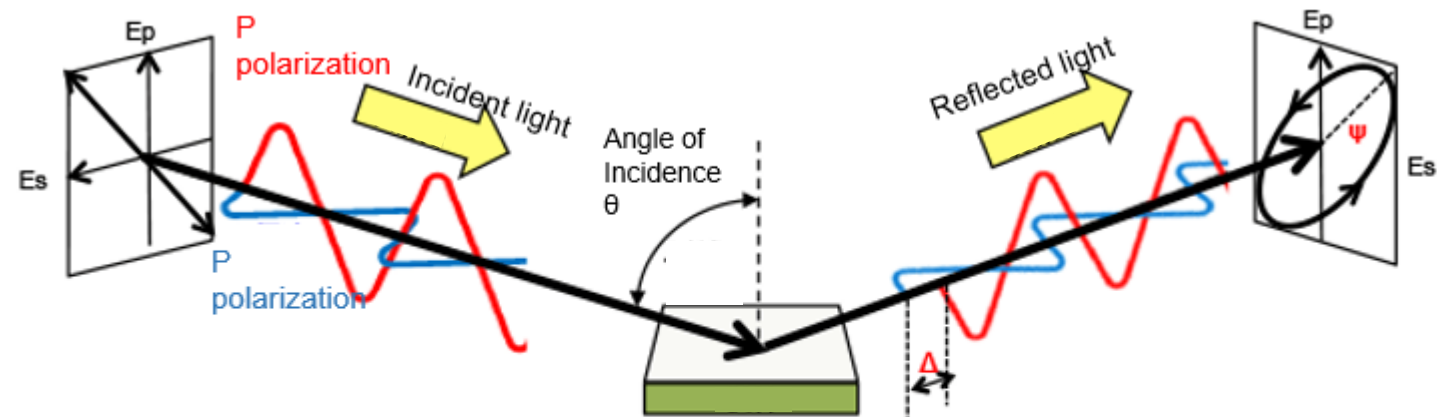
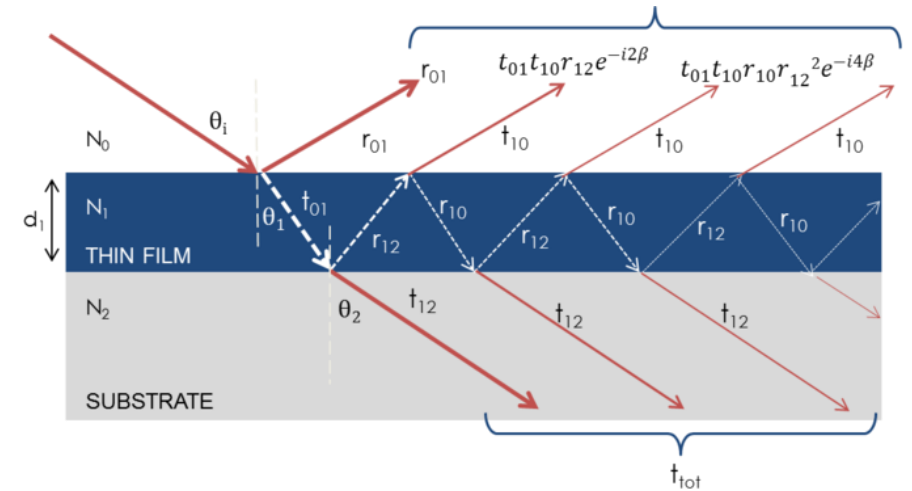
Absorption Spectroscopies

- For static approaches, x-ray techniques are the most powerful (XAS, NEXAFS). Time-resolved approaches can be done with lower energy photons
- Very sensitive to local atomic arrangements, oxidation states, etc.
- For absorption, samples should be thin (consider: x-ray damage, signal-to-noise...). Usually, reflective geometry can also be an option for thicker samples
- Signals can be surprisingly complex to analyze! Energy shifts and pre-edge features hold the desired information



Ellipsometry

- Used for probing the optical properties of thin films (complex refractive index, dielectric function)
- ! Note assumption that sample is optically homogeneous, isotropic, and not rough on surface



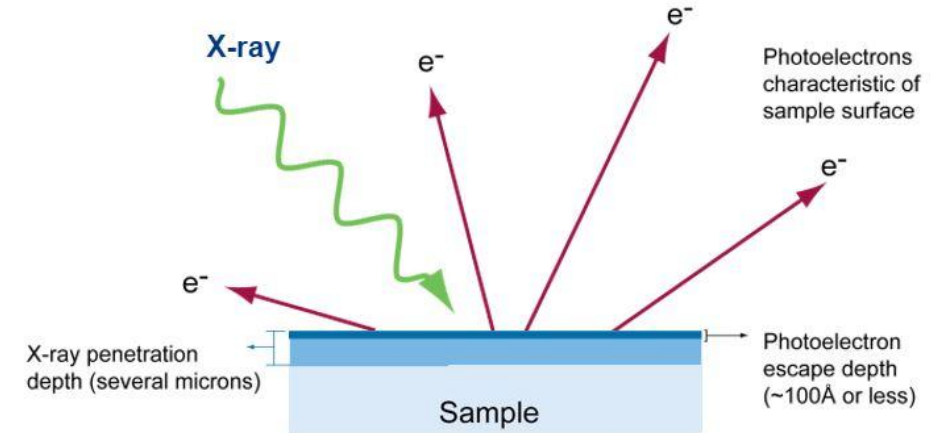
Measures changes in polarization state of incident light and reflected light

Δ : Phase difference between S polarization and P polarization

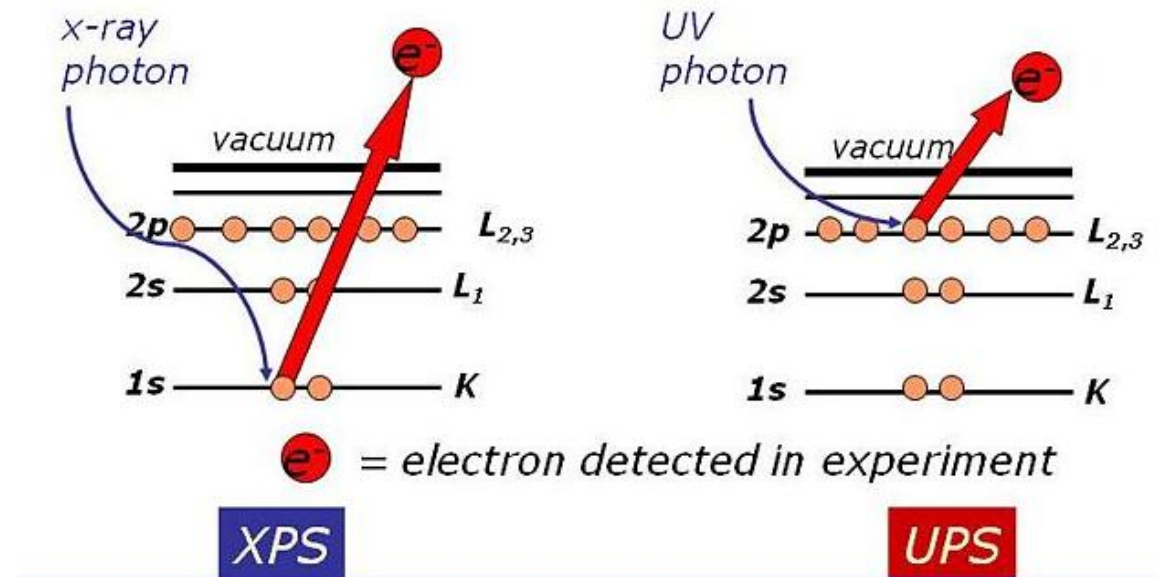
Ψ : Reflection amplitude ratio angle of S polarization and P polarization

Photoemission – XPS/UPS

- Sensitive probe of the occupied energy levels of a material
- Ultraviolet UPS typically done at 21 eV (He lamp)
- Higher energy XPS (e.g., Al K α) is element-specific – exact recorded energies of core levels are sensitive to local environment
- Requires ultrahigh vacuum environment
- Likely easy to access basic capabilities

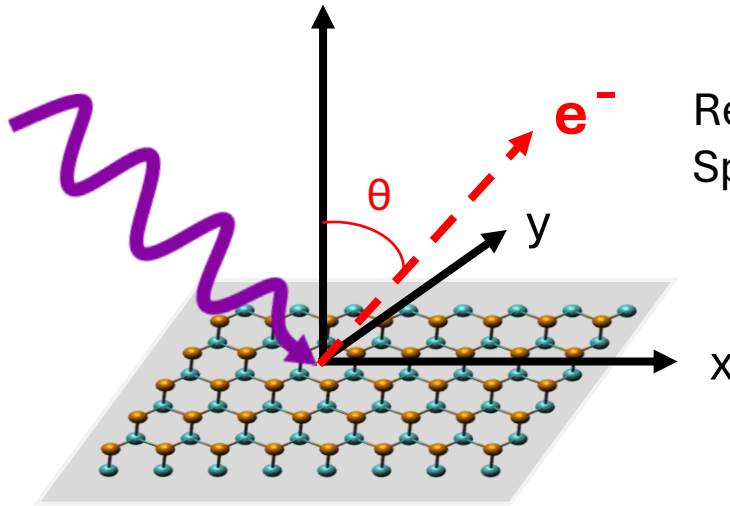


euofins



Photoemission - ARPES

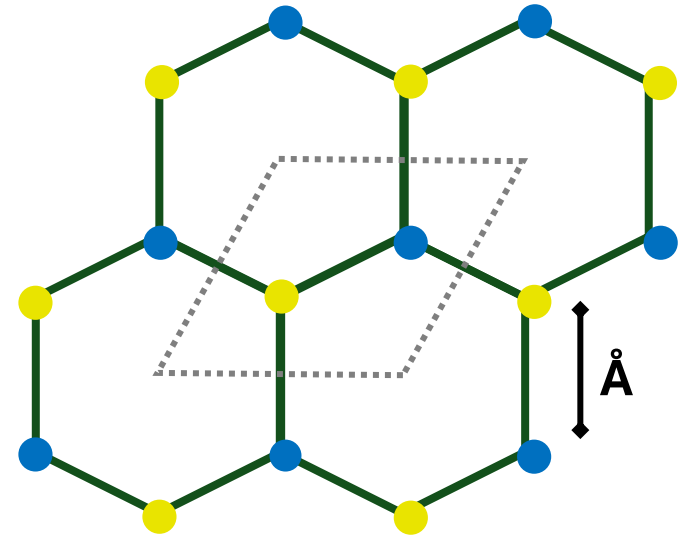
- Photon in, electron out technique that directly records momentum space information by recording angles of emission
- Ultrahigh vacuum technique; very surface sensitive
- Requires a single crystalline sample with clean surface and not too insulating material or conductive substrate
- Can be performed with a high energy lamp light source, but specialized equipment typically means going to a synchrotron



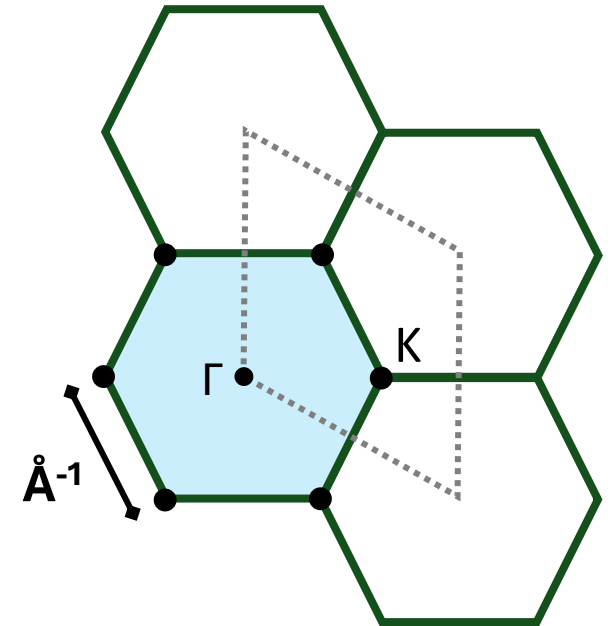
$$E_{kin} = h\nu - W - E_B$$

$$k_{\parallel} = (2m_e E_{kin})^{1/2} \sin \theta / \hbar$$

Real
Space

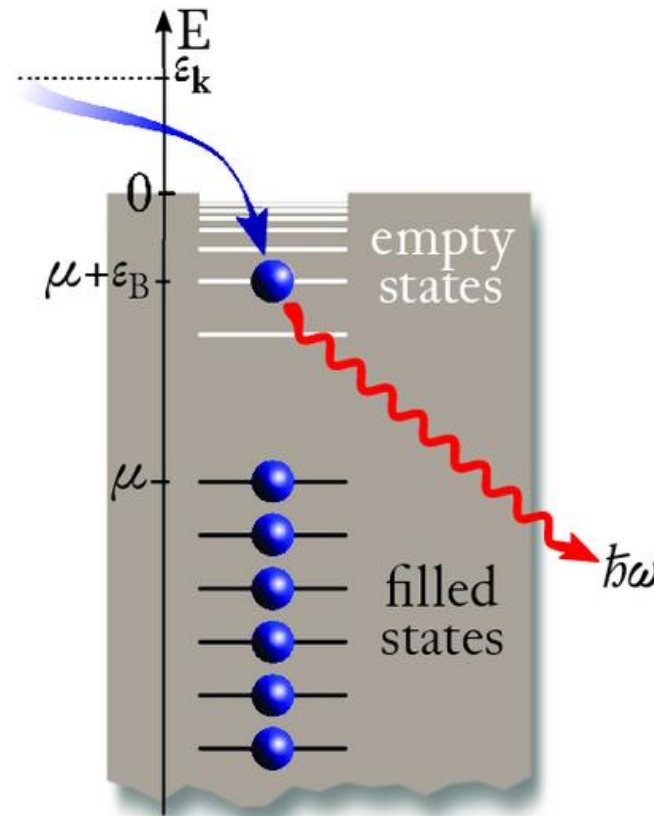


Reciprocal
Space



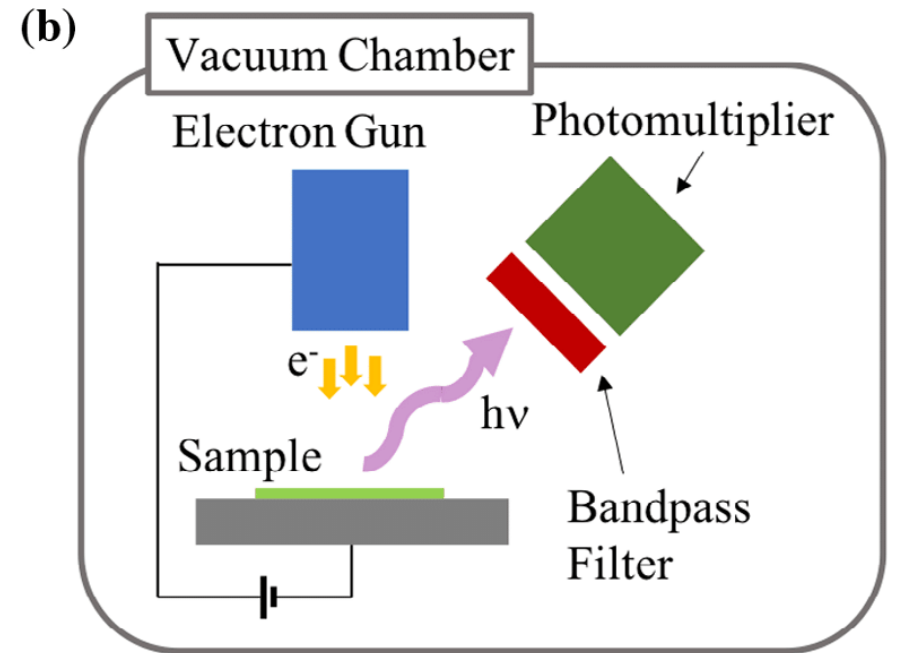
Inverse Photoemission Spectroscopy

- Electron in, photon out technique
- Monochromatic electron source impinges on the sample, a small number relax into formerly unoccupied states by emission of a photon
- Relatively simple way to record basic excited state energy information if time resolution is not needed and coarse energy resolution is OK (~ 1 eV)



IPES

Marco Vanzini



S. Kim et al., *Science and Technology of Advanced Materials*
2018, 19(1):486-494

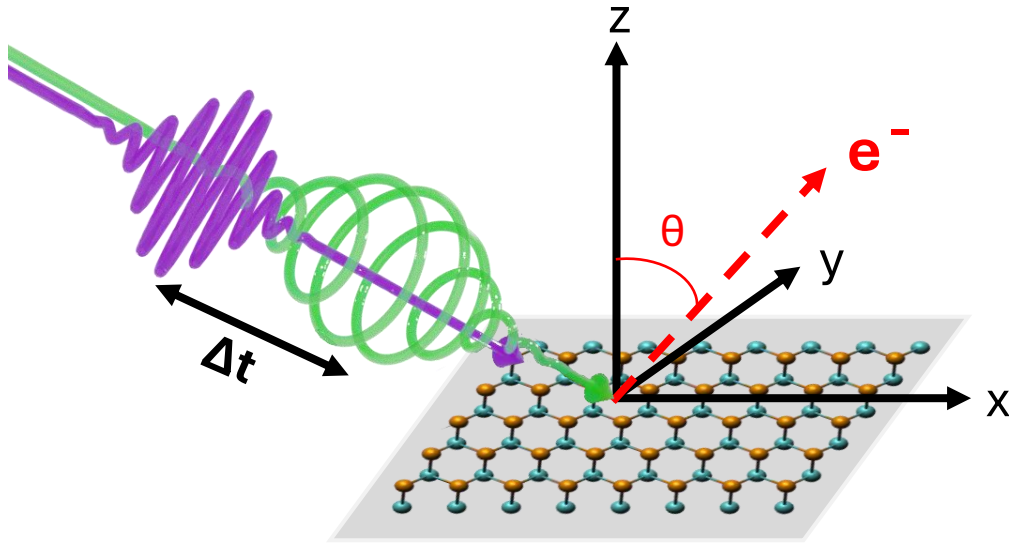
Which characterization technique is the right one for my material?

That depends a great deal on what it is you want to learn!

Much more that lies beyond this talk!
(Come talk to me about time-resolved spectroscopies)

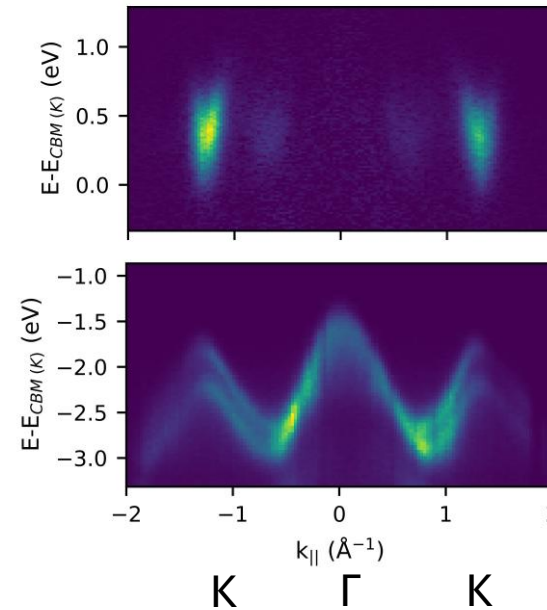


Time-resolved photoemission

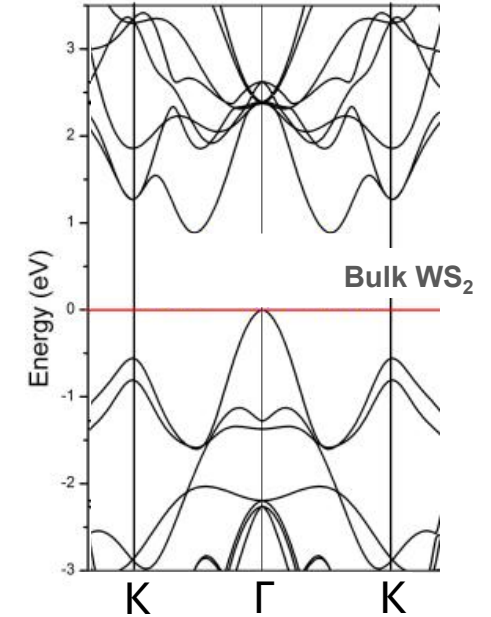


$$E_{kin} = h\nu_{probe} - W - E_{BE}$$

$$k_{||} = (2m_e E_{kin})^{1/2} \sin \theta / \hbar$$



A. Kunin et al. *Phys. Rev. Lett.* **130**, 046202 (2023)



H. Terrones et al. *Sci Rep.* **3**, 1549 (2013)

- Directly visualize electrons (and holes, as depletion) in momentum space and map the occupied band structure vs. time
- Space charge effects typically become limiting factor for energy resolution and sensitivity